



《风光欣》技术资料

MCR100-8 SILICON PLANAR PNP THYRISTOR

FEATURES

Current-IGT: 200 μ A

I_{TRMS} : 0.8A

V_{DRM} : MCR100-8: 600V

Operating and storage junction temperature range

T_j, T_{stg} : -55 to +150



TO-92

1.CATHODE

2.GATE

3.ANODE

ELECTRICAL CHARACTERISTICS ($T_{amb}=25$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit	
On state voltage	V_{TM}	$I_{TM}=1A$		1.7	V	
Gate trigger voltage	V_{GT}	$V_{AK}=7V$		0.8	V	
Repetitive peak off-state voltage	V_{DRM}	$I_{CRM}=10 \mu A, V_{MAX}=1010V$	600		V	
Peak forward or reverse blocking current	I_{DRM}	$V_{AK} = \text{Rated}$		10	μA	
	I_{RRM}	V_{DRM} or V_{RRM}				
Holding current	I_H	$I_{HL}=20 mA, A_V = 7V$		5	mA	
Gate trigger current	I_{GT}	$V_{AR}=7V$	A2	5	15	μA
			A1	15	30	μA
			A	30	80	μA
			B	80	200	μA